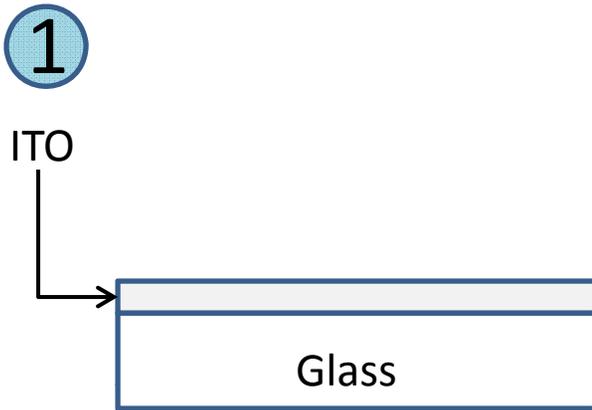
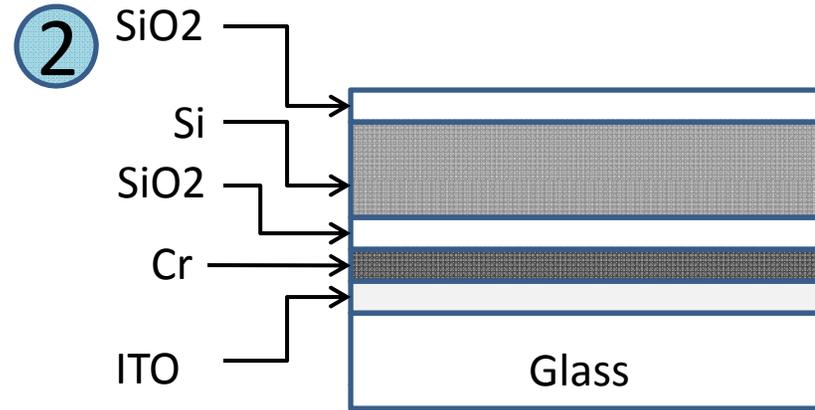


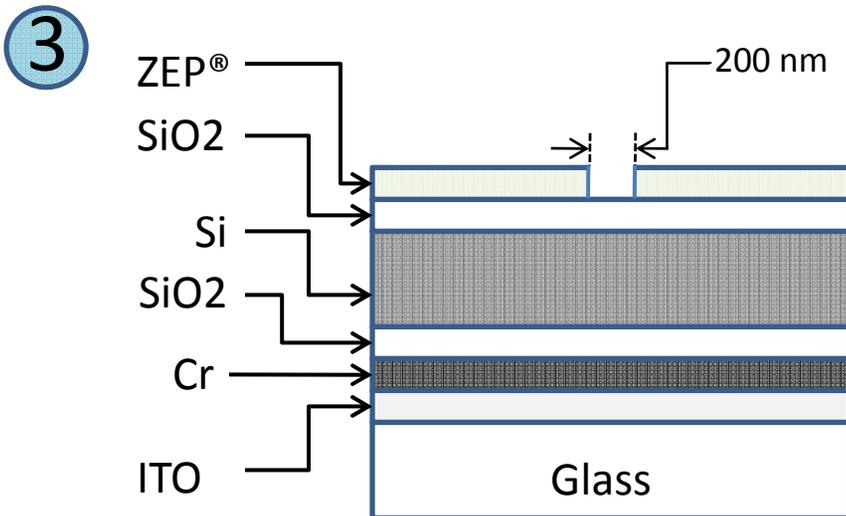
Electractive Nanowells Fabrication



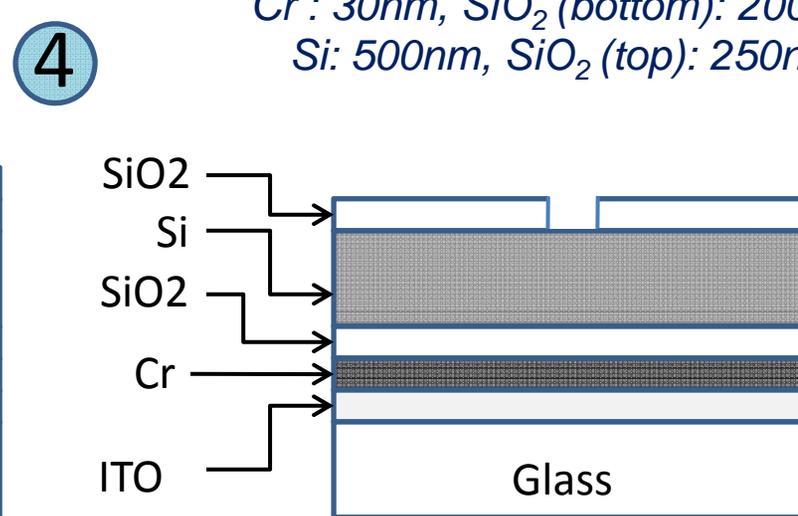
ITO Coated Coverslip



Cr Evaporation and PECVD:
*Cr : 30nm, SiO₂ (bottom): 200nm,
Si: 500nm, SiO₂ (top): 250nm*

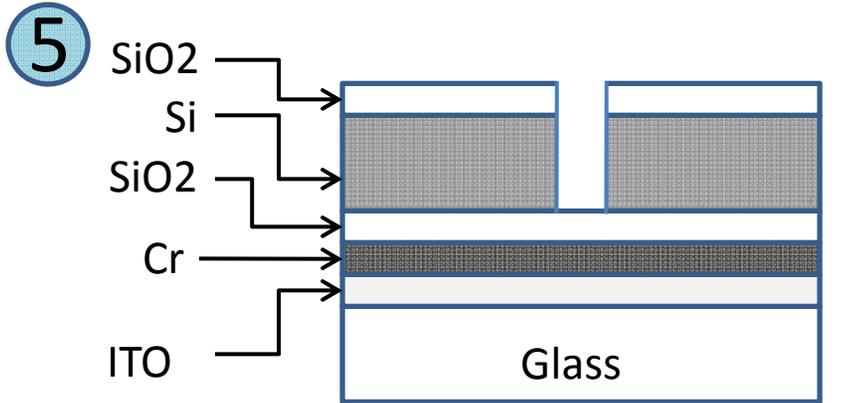


ZEP® Electron Beam resist spin (250nm), exposure and development

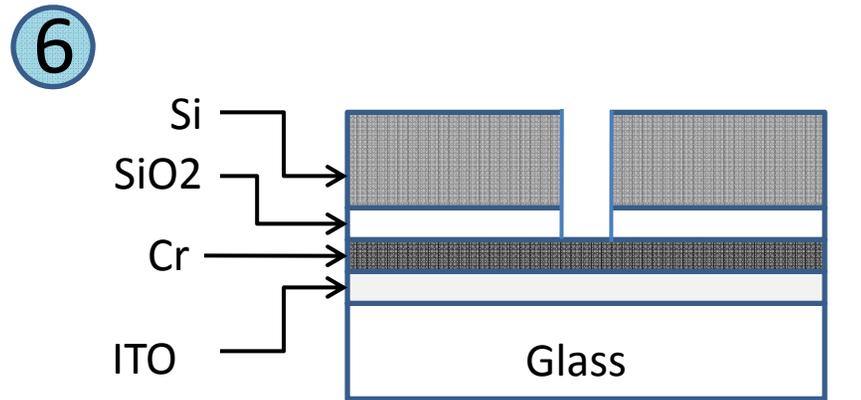


CHF₃/AR Oxide Etch (ZEP is etched entirely)

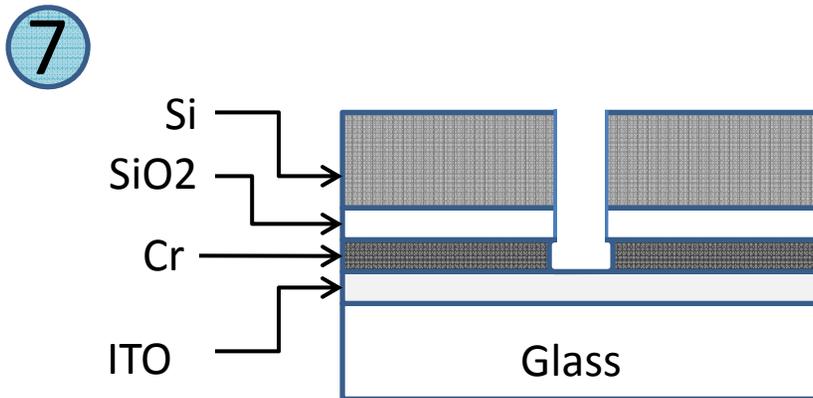
EANW Fabrication, Continued



*ICP RIE Etch of Silicon:
Chlorine type SF₆ etch*



CF₄ RIE etch of bottom SiO₂



Cr Wet Etch

SEMS Electroactive Nanowells

